

SUSS SOLUTIONS FOR LARGE FORMAT PATTERNING UV Scanning Lithography and Excimer Laser Ablation



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MARKET DRIVER

Mobile Applications drive Advanced Packaging Development.

- + Small Form Factor
- + High Performance
- + High Bandwidth
- + Low Power Consumption
- + Low Cost
 - Smaller L/S and Via
 - Higher I/O count
 - Higher Yield
 - Higher Reliability
 - + Higher Performance+ Lower Cost

PC and Mobile Product Growth





Source: TechSearch International, Inc. from various sources, including IDC PC, Media Tablet and Mobile Phone Trackers, March 2012



SUSS MicroTec's patterning solution: UV Scanner and Excimer Laser Ablation System

AP INFRASTRUCTURE ROADMAP

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- + All platforms may coexist.
- 450mm being slow, panel based packaging will grow.
- Each sector has different benefits.
 - OSAT, IDM: FOWLP
 - Substrate Manufacturer: Embedded Die
- + Same requirements: Cost, Size, Performance
- + Collaboration required for reliable infrastructure







Yole Developpement 2012

FRANKLER.

HUSSON

LARGE PANEL ADVANTAGES

- + Wafer vs. Panel: technology dependent
- + Rectangular: natural choice for better fit and surface utilization
- + Throughput: reduced handling/transfer time
- + Standards and Infrastructure
 - Process and equipment
 - Size
 - Material







PHOTOLITHOGRAPHY VS. DIRECT ABLATION

+ Photolithography

- Proven technology
- Resolution limitation
- Multistep process
- Hazardous/environmentally unfriendly wet chemical process
- Balance of the photo characteristics with the desired thermal/mechanical properties of the material
- Cure of the polymer after photo-process

+ Excimer Laser Ablation

- Direct material removal according to the mask pattern
- Simpler process without wet develop step
- Fine via with high aspect ratio
- Material properties not limited by the need of photo-imaging
- Cure of the polymer before laser processing







SUSS EXPOSURE PRODUCT PORTFOLIO

SUSS MicroTec

Mask Aligner



MA200 Gen3 Automatic 150/200mm



MA300 Gen2 Automatic 200/300mm



DSC300 Gen2 Automatic 200/300mm



ELP300 Gen2 Automatic 200/300mm

Projection Scanner Excimer Ablation System



MA/BA8 Gen3 Semi-Automatic Pieces up to 200mm



MA12 Manual 200/300mm (squares)



DSC500 / DSC800 Automatic 450x500mm / 650x780mm



ELP600 Automatic 600x600mm

DSC300/500/800 UV PROJECTION SCANNER

SUSS MicroTec

- + Proven UV projection scanning technology
- + Low cost
- + Full-Field No-Stitch 1:1 Projection Imaging
- + Alignment accuracy: TSA < 1μm
- + Variable NA high DoF to high resolution
- + Full automation
- + Wafers: 200mm, 300mm, 450mm
- + Panels: 450x500mm, 650 x 780mm



DSC500: Near Vertical Orientation



DSC300 Beam Delivery System



DSC 300 - Wafers



DSC PROJECTION SCANNER IMAGING EXAMPLES



30µm vias in 100µm WBR2100



40μm vias in 80μm AZ125nXT



5µm vias in 10µm AZ10XT



6μm and 7μm L/S in 15μm AZ4620



6μm vias in 10μm HD8820 PBO



10μm L/S in 12μm AZ15nxT

ELP 300/600 EXIMER ABLATION SYSTEM

- + ELP300: up to 300mm wafer
- + ELP600: up to 600mm x 600mm substrate





EXCIMER LASER ABLATION

- + 248nm and 308nm
- Direct removal of the material
 - Add enough energy to break the molecular bonds at the surface.
 - Limited thermal effect for heating or change to adjacent area or underlying material.
- Mask based projection
- + Throughput independent of the pattern shape or density.

Suitable Materials:

- + Most organic materials
 - Polymers/Organic Dielectrics (PI, PBO, BCB, Epoxy etc.)
 - Epoxy Mold Compounds (EMC filled and unfilled)
- + Some inorganics
 - Dielectrics (SiNx < 1µm thick with 248nm)
 - Thin metals (Ti, TiW, TaN, Ta, Cu, Ag, Al, etc. < 600nm thick on organic material)
 - Conductive materials (ITO, IZO, CNT < 1µm thick on organic material)



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EXCIMER LASER ABLATION

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- + Fluence and Etch Rate
 - With threshold fluence $F_0 \sim \text{constant}$ etch depth per pulse (etch rate) can be predicted.
 - Depth control by number of pulses
- + Metal Pad as Etch Stop
 - Metal pads (> ~1µm) become natural stop layer for Excimer via ablation.
 - Flexibility for material thickness variation.





Y. H. Chen, H. Y. Zheng, K. S. Wong, and S. C. Tam, "Excimer laser drilling of polymers", Proc. SPIE 3184, 1997



Cu Pad

Via 30µm

Al Pad





WAVELENGTH, FLUENCE, PULSE, AND ETCH RATE

+ Absorption and etch rate vary:

- Wavelength
- Fluence
- + Etch depth control by number of pulses



0.6

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SIDE-WALL ANGLE AND FLUENCE

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- + Side-wall Angle controlled by Fluence
 - Steeper wall with higher fluence
 - Higher etch rate with higher fluence



376 mJ/cm², 45 pulses

1200 mJ/cm², 12 pulses



EXCIMER LASER ABLATION ADVANTAGES

+ Technical benefits

- Higher via resolution < 3µm (2µm demonstrated)
- High overlay control:
 - 300mm Wafer: +/- 1µm
 - Panels: +/- 2µm
- Side-wall angle control
- Limited thermal effect
- + Simpler process
 - Eliminate develop and chemical etch steps
 - Reduce bake/curing step
- + Safety and environmental protection
 - Reduction of hazardous process steps and chemicals
 - Reduction of chemical waste
- + Benefit with Non-Photo Material
 - Cost Reduction
 - Combination of desirable material properties



+ Non-photo material's advantages

- Desirable properties
- Low cost

| Photo/Non-Photo | Non-Photo | Photo |
|------------------------|-----------|----------|
| Material | PI | PI |
| Manufacturer | HD Micro | HD Micro |
| Product | PI-2611 | HD-4100 |
| CTE (ppm/°C) | 3 | 35 |
| Modulus (GPa) | 8.5 | 3.4 |
| Tensile Strength (MPa) | 350 | 200 |
| Elongation (%) | 100 | 45 |

ELP600 – TECHNICAL CHARACTERISTICS

| Beam Delivery System | |
|-------------------------------|--|
| Wavelength | 248nm and 308nm |
| Projection Lens | 2.0x, 2.5x & 5x reduction (up to 100mm diameter) |
| resolution | vias to ~3 μm ; Traces to ~5 μm (material & depth dependent) |
| Processing Methods | |
| Ablation Methods | Step & Repeat; Step & Scan; Continuous Scan |
| Alignment System | |
| Туре | Global and site-to-site; Auto pattern recognition |
| Top Side Alignment | <± 2.0µm |
| BSA | < ± 3.0µm (future option) |
| Auto alignment | yes |
| Manual alignment | yes |
| Substrate Handling | |
| Substrate loading | Manual (Auto loading option) |
| Mask loading | Manual (Auto loading option) |
| Substrate Size | Up to 600mm x 600mm |
| Mask | 177.8 x 177.8mm, 3.8mm thickness |
| Carrier Mounted Substrates | Yes |
| Thin substrates w/o Carrier | Thickness down to 250µm |
| System Enclosure | |
| debris removal system | vacuum, external exhaust; (reclaim system option) |
| safety enclosure | interlocked enclosure for Class 1 Laser Safety |
| environmental control | ECU (+/- 0.5deg C); HEPA filters |
| Dimensions | |
| Main System (Height x Width x | ~2500mm x 2300mm x 2680mm (excluding ECU, Laser & |
| Depth) | auto substrate loader) |
| Weigtht (BDS) | ~3500 kg |





ELP EXCIMER STEPPER PATTERNING EXAMPLES (PHOTO MATERIAL)

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JSR WPR 5100 10µm





HD8930 PBO 13µm





HD4004 8.2µm



40 µm vias



15 µm dia vias

ELP EXCIMER STEPPER PATTERNING EXAMPLES (NON-PHOTO MATERIAL)

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EMC (undisclosed) 10µm







HD (proprietary) 8µm



HD2574





Dow BCB Cyclotene 302X 12µm







ELP EXCIMER STEPPER PATTERNING EXAMPLES (BCB CROSS SECTION)

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 Mask:
 7 μm

 Top:
 6 μm

 Bottom:
 4.2 μm

 650 mJ/cm²



 Mask:
 5 μm

 Top:
 4.1 μm

 Bottom:
 2.6 μm

 650 mJ/cm²

Michael Töpper, Karin Hauck, Mario Schima Danny Jaeger, Klaus-Dieter Lang, "A sub-4 µm Via Technology of Thin film Polymers using Scanning Laser Ablation", ECTC 2015



ELP EXCIMER STEPPER PATTERNING EXAMPLES (BCB DRY FILM CROSS SECTION)

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IZM



 Mask:
 10 μm

 Top:
 10.3 μm

 Bottom:
 7.2 μm

 Thickness:
 15 μm



 Mask:
 5 μm

 Top:
 4.7 μm

 Bottom:
 2.8 μm

 Thickness:
 15 μm

Michael Töpper, Karin Hauck, Mario Schima Danny Jaeger, Klaus-Dieter Lang, "A sub-4 µm Via Technology of Thin film Polymers using Scanning Laser Ablation", ECTC 2015

ELP EXCIMER STEPPER PATTERNING EXAMPLES (FILLED VIA AND RDL)



2 metal layer with 10µm fully filled micro-vias at 40µm pitch and 2.5µm line



8-10µm fully filled micro-vias at 20µm pitch

Yuya Suzuki, Jan Brune, Rolf Senczuk, Rainer Pätzel, Ryuta Furuya, Fuhan Liu, Venky Sundaram, Rao Tummala, "Demonstration of 20µm Pitch Micro-vias by Excimer Laser Ablation in Ultra-thin Dry-film Polymer Dielectrics for Multilayer RDL on Glass Interposers", ECTC 2015 **Georgia Tech PRC ZEON**

POST LASER ABLATION CLEANING

+ Post ablation cleaning is required for subsequent processes in most cases.

- Sacrificial layer
 - + Successful cleaning of HD4104
 - + Sacrifiall layer removed with high-pressure CO₂ ionized water

O₂ plasma cleaning

- + Successful cleaning of PBO, BCB, HD2611, HD4110
- + In-house tool (vacuum plasma) available

CO₂ snow cleaning

- + Successful cleaning PBO with most aggressive CO₂ snow
- + 3rd party tool available

DPSS Cleaning

- + Successful cleaning PBO (HD8820)
- + Using pico second DPSS Laser
- + In-house tool available

+ The material determines the cleaning method.



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after

Sacrificial Layer



before









DPSS

SUMMARY

- + Mobile products drive packaging trend
 - Cost, Form Factor, Performance, Yield
- + Large size rectangular panel will grow for high volume manufacturing.
 - Driven by cost reduction
- + Patterning is a major factor along with material development.
 - Suss MicroTec provides Mask Aligner, UV Projection Scanner and Excimer Laser Ablation for patterning applications.
 - UV scanner and excimer laser stepper are available for large format patterning.
 - Excimer laser stepper provides maximum benefits with non-photo materials.
 - Excimer laser stepper applications in RDL Via and Trench formation, SLR and Laser Debonding.
- + Demo and evaluation test available
 - In-house at Suss MicroTec
 - Fraunhofer Institute IZM



Thank you